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(54) **SEMICONDUCTOR PACKAGES WITH
CHIPLETS COUPLED TO A MEMORY
DEVICE**

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25/0655; H01L 25/072; H01L 25/0753;
H01L 25/115; H01L 2924/1434; H01L
45/14; H01L 45/145; H01L 45/1691;
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2201/01; H05K 2201/0195; H05K
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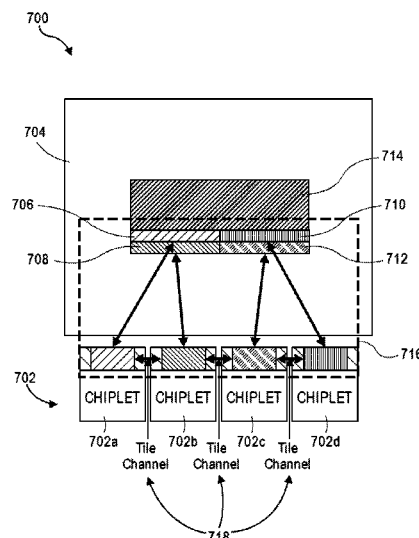
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(57) **ABSTRACT**

Apparatuses, devices and systems associated with semicon-
ductor packages with chiplet and memory device coupling
are disclosed herein. In embodiments, a semiconductor
package may include a first chiplet, a second chiplet, and a
memory device. The semiconductor package may further
include an interconnect structure that couples the first chiplet
to a first memory channel of the memory device and the
second chiplet to a second memory channel of the memory
device. Other embodiments may be described and/or
claimed.

24 Claims, 11 Drawing Sheets



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See application file for complete search history.

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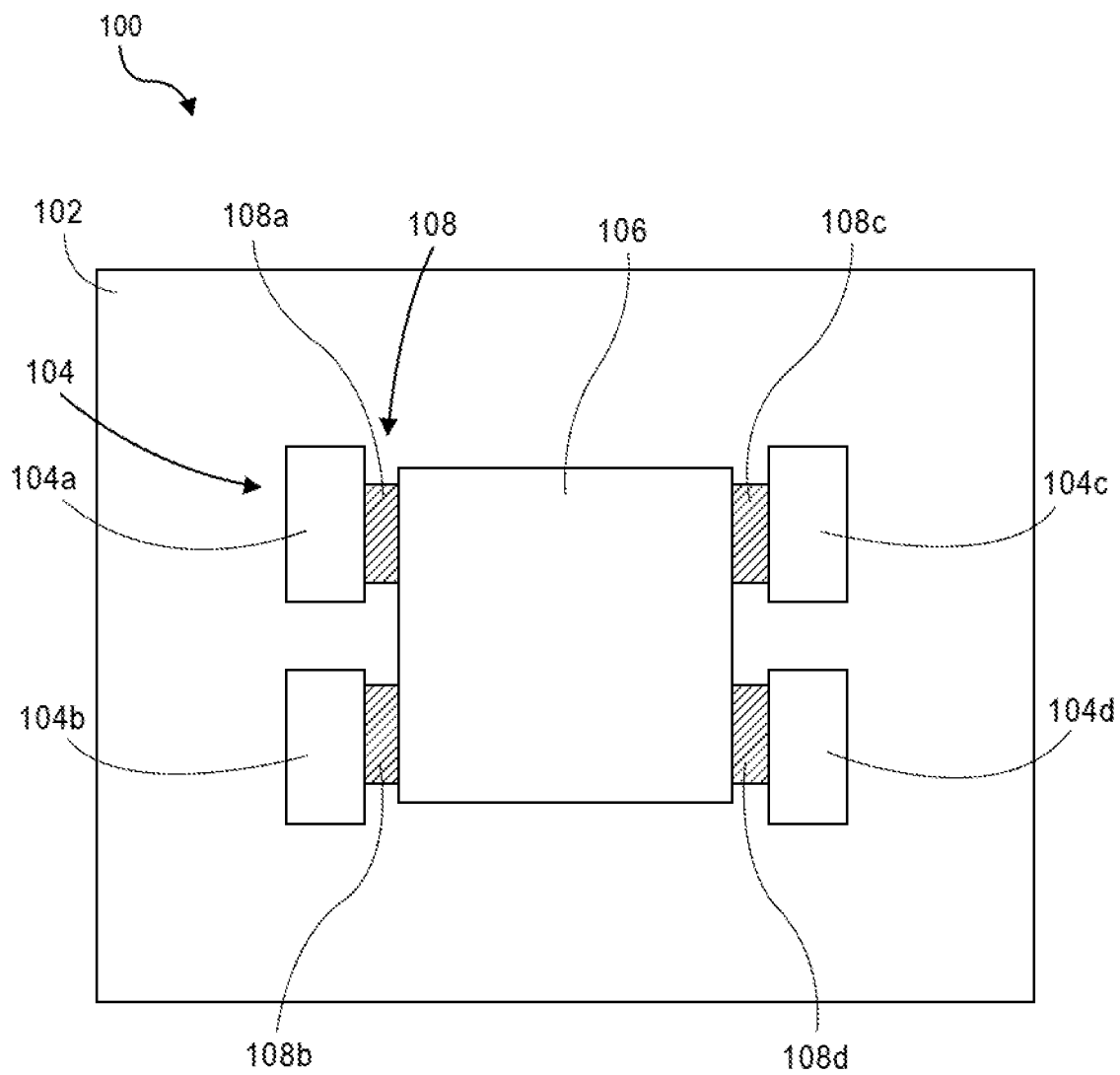


FIG. 1

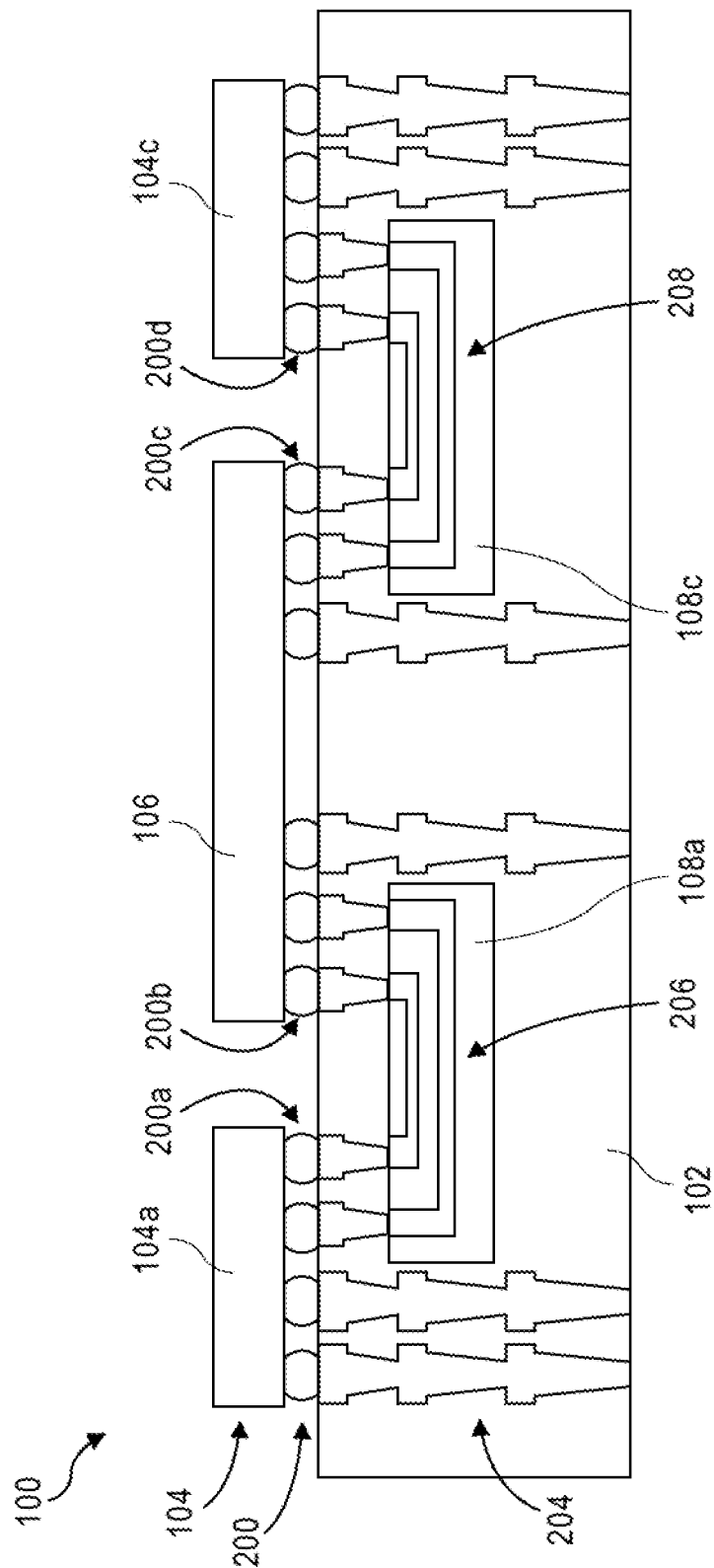


FIG. 2

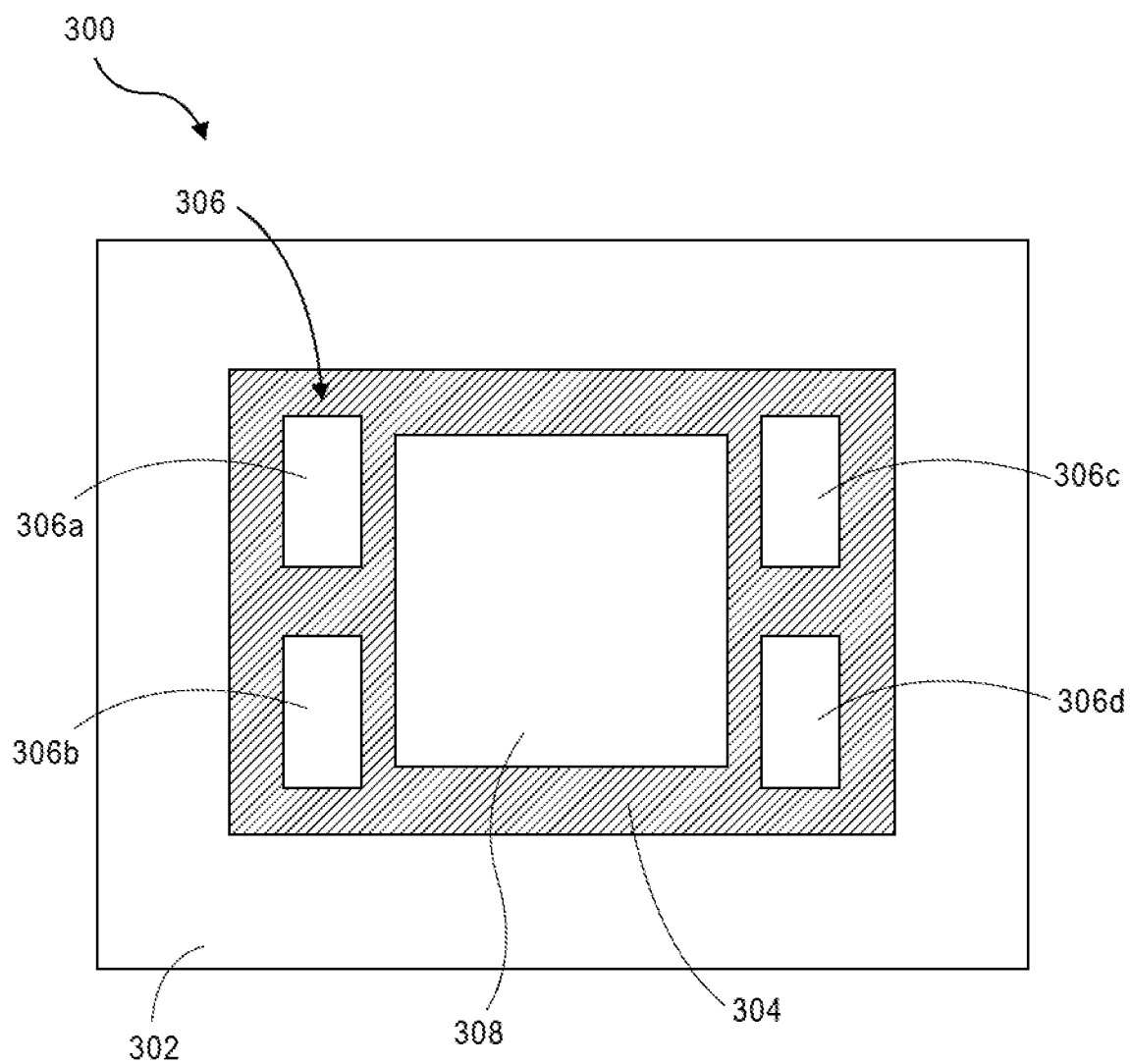


FIG. 3

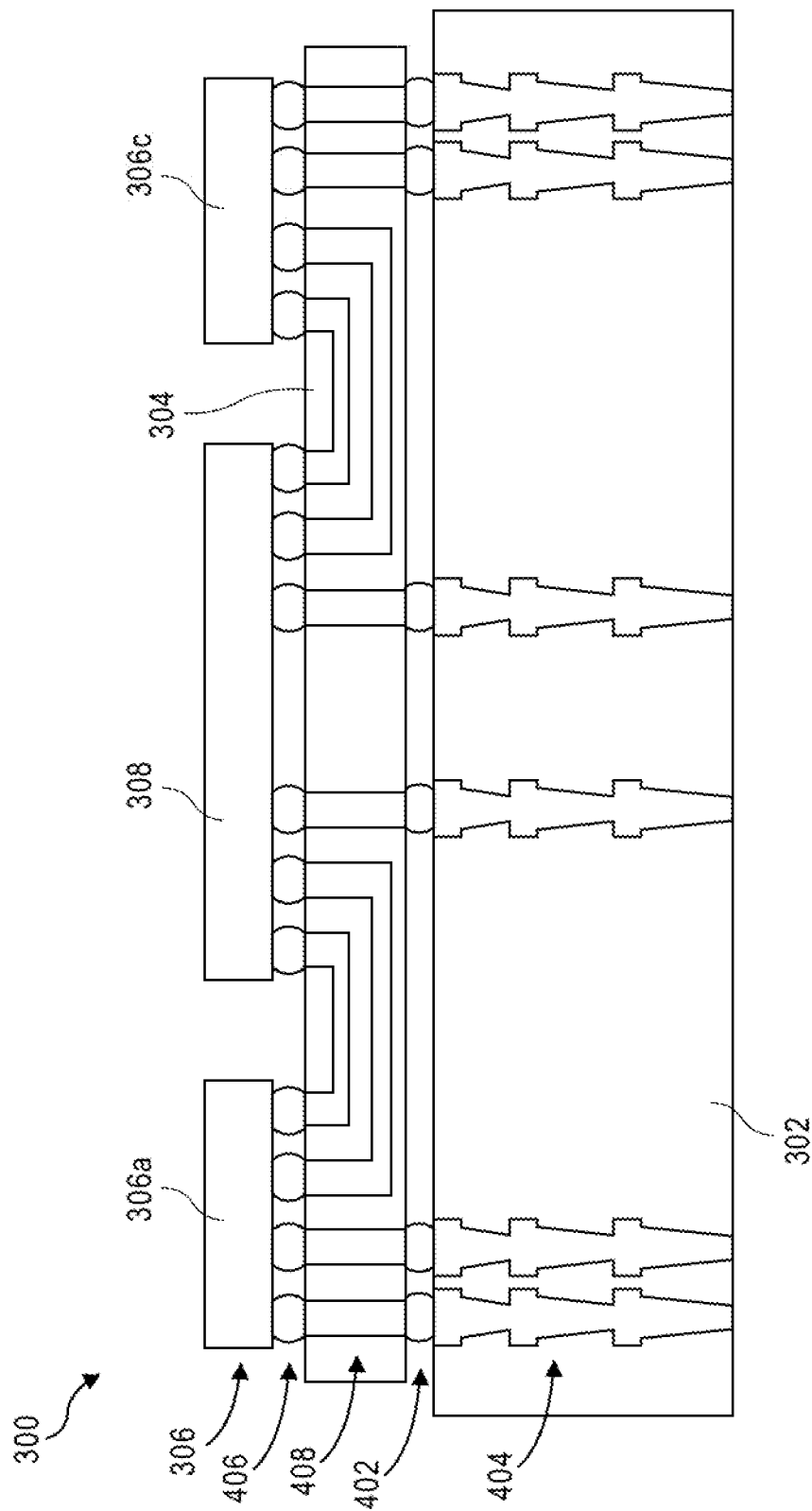


FIG. 4

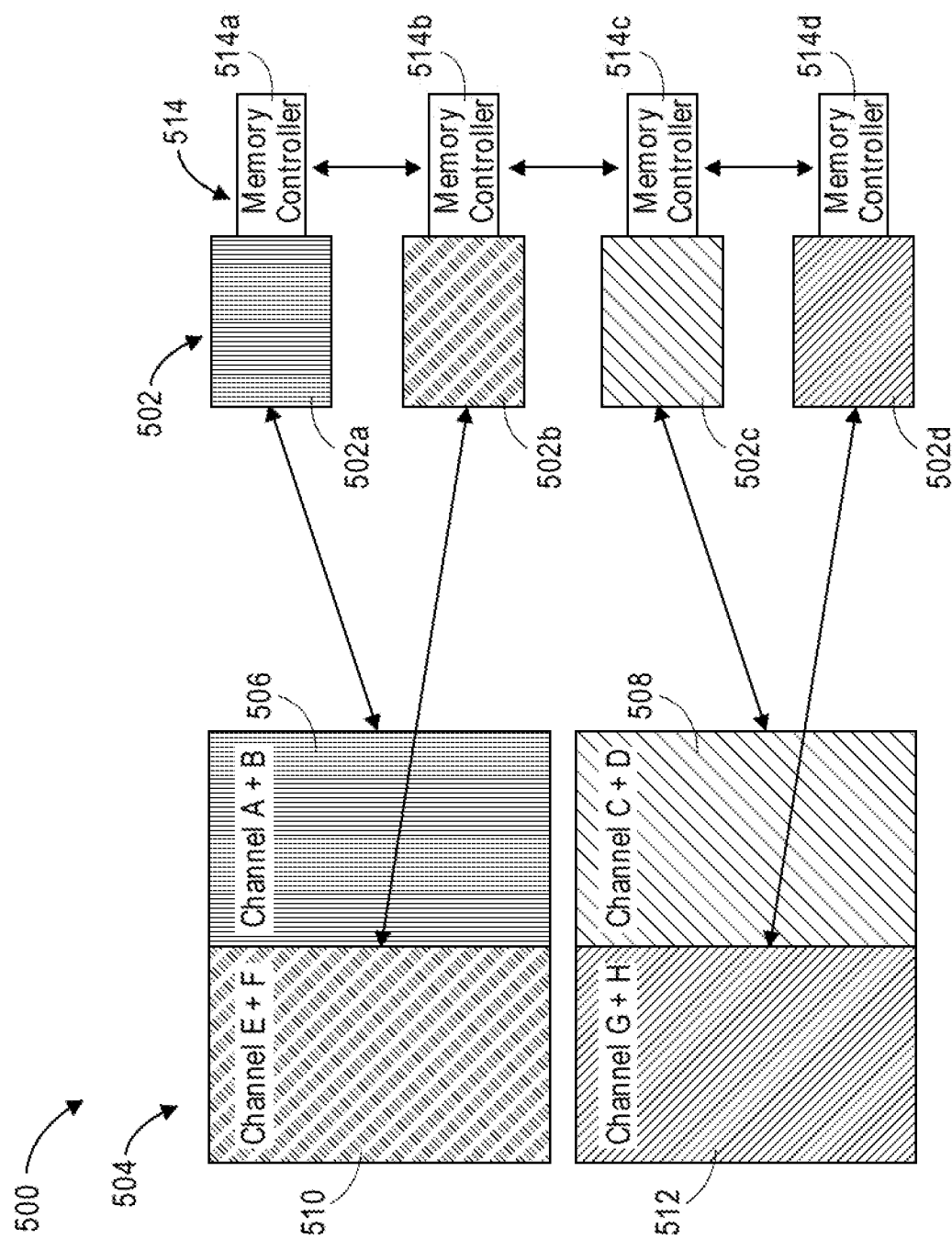


FIG. 5

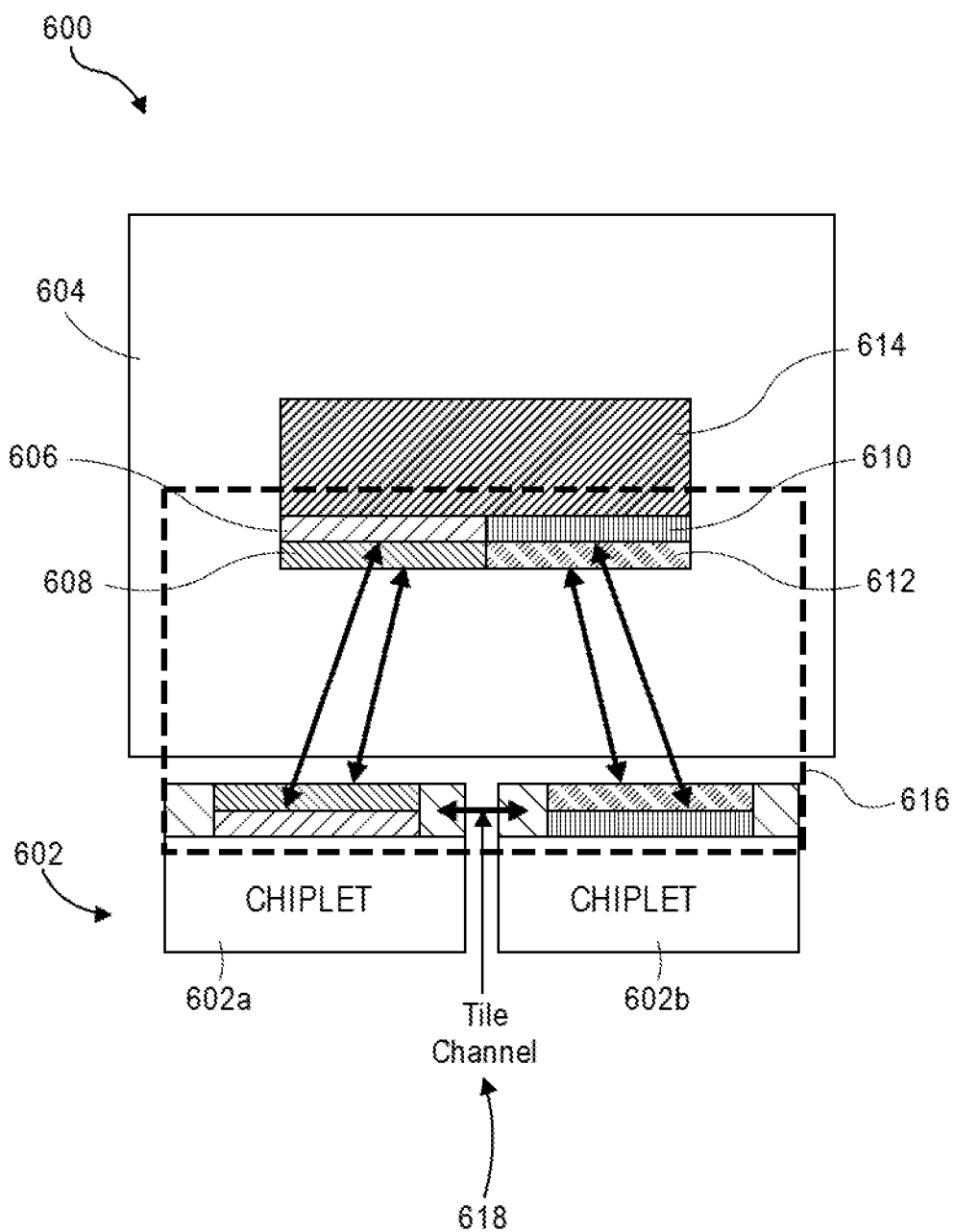


FIG. 6

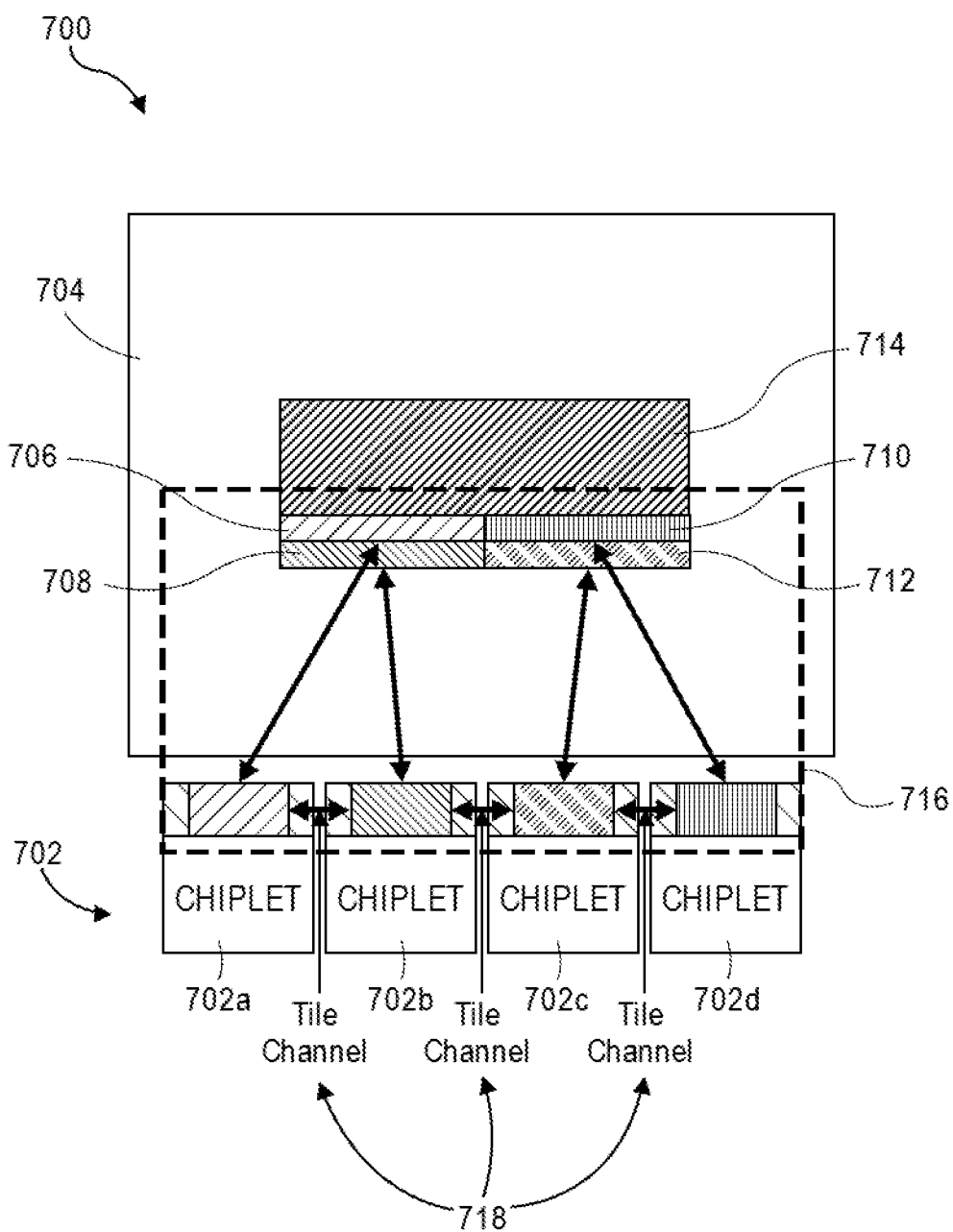


FIG. 7

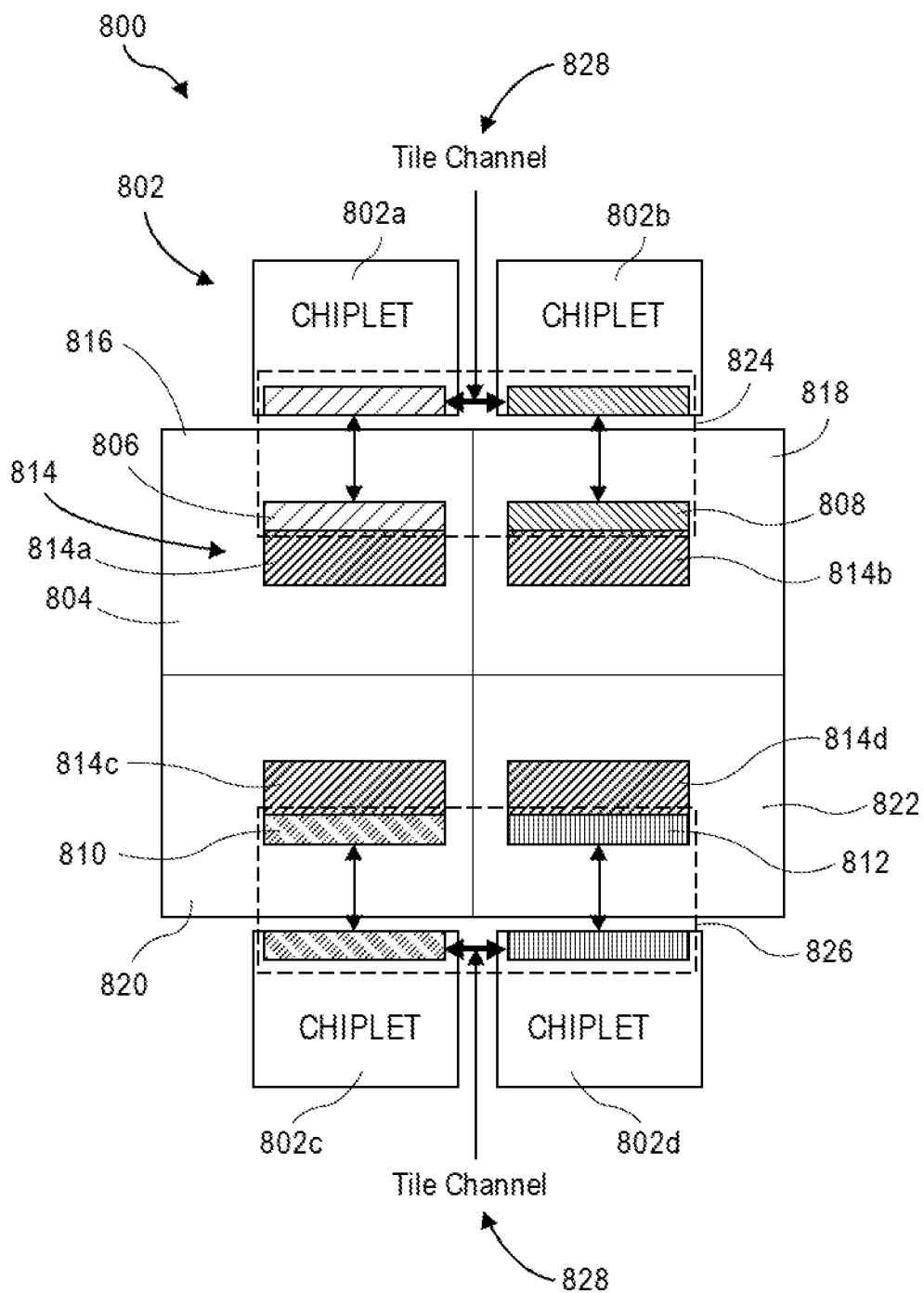


FIG. 8

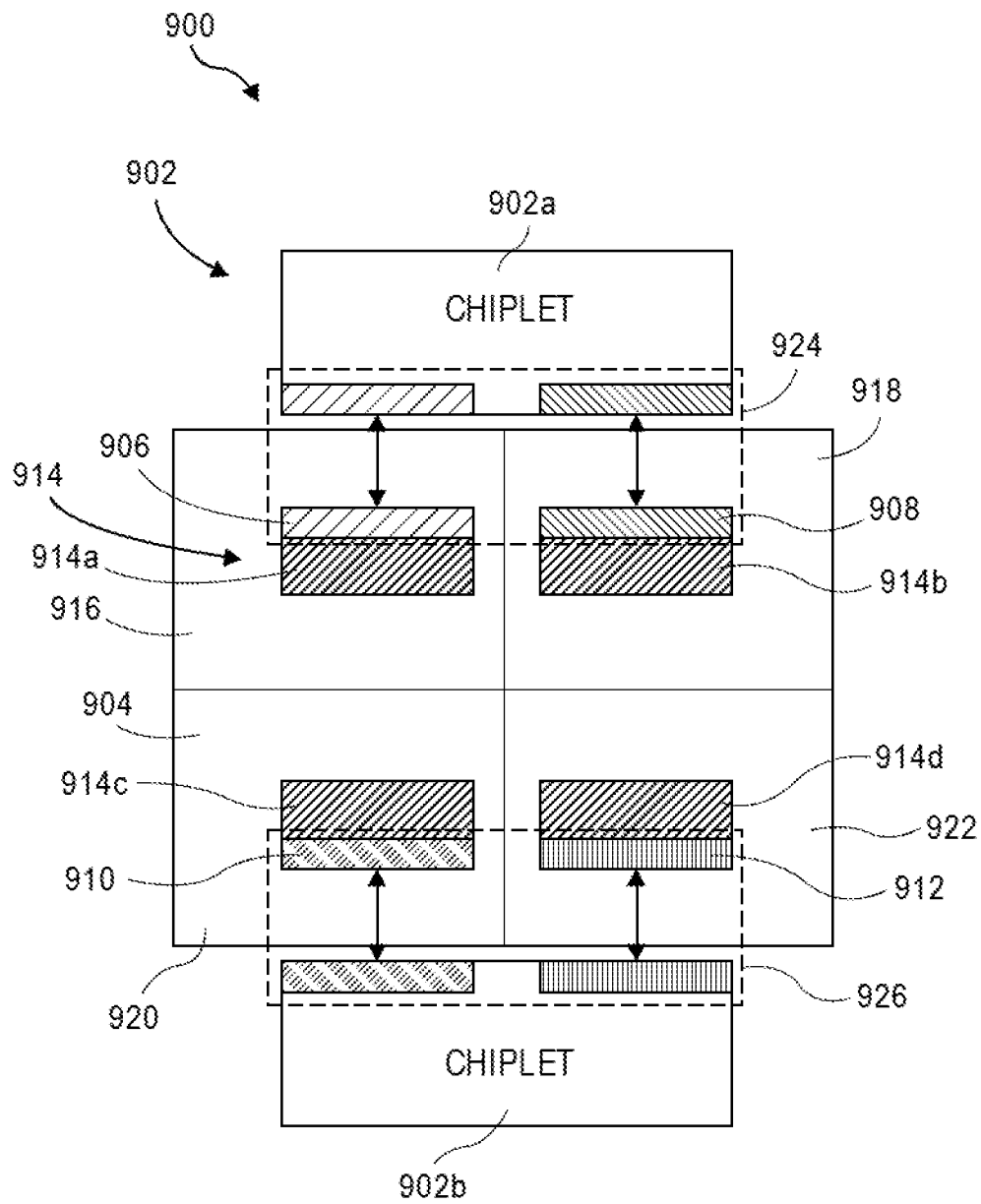


FIG. 9

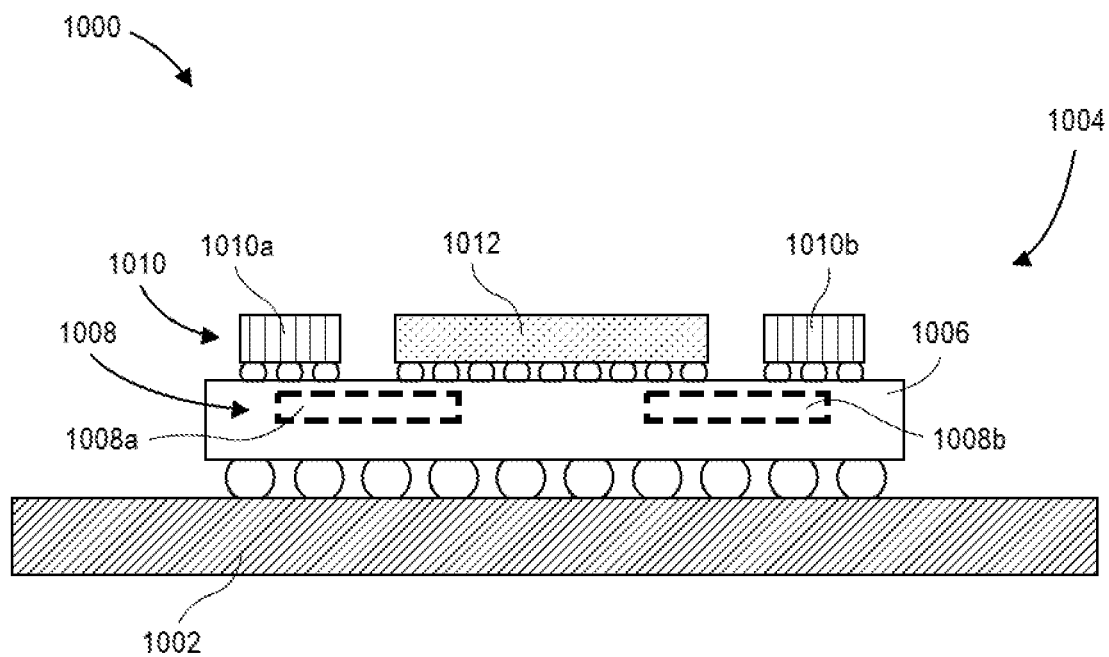
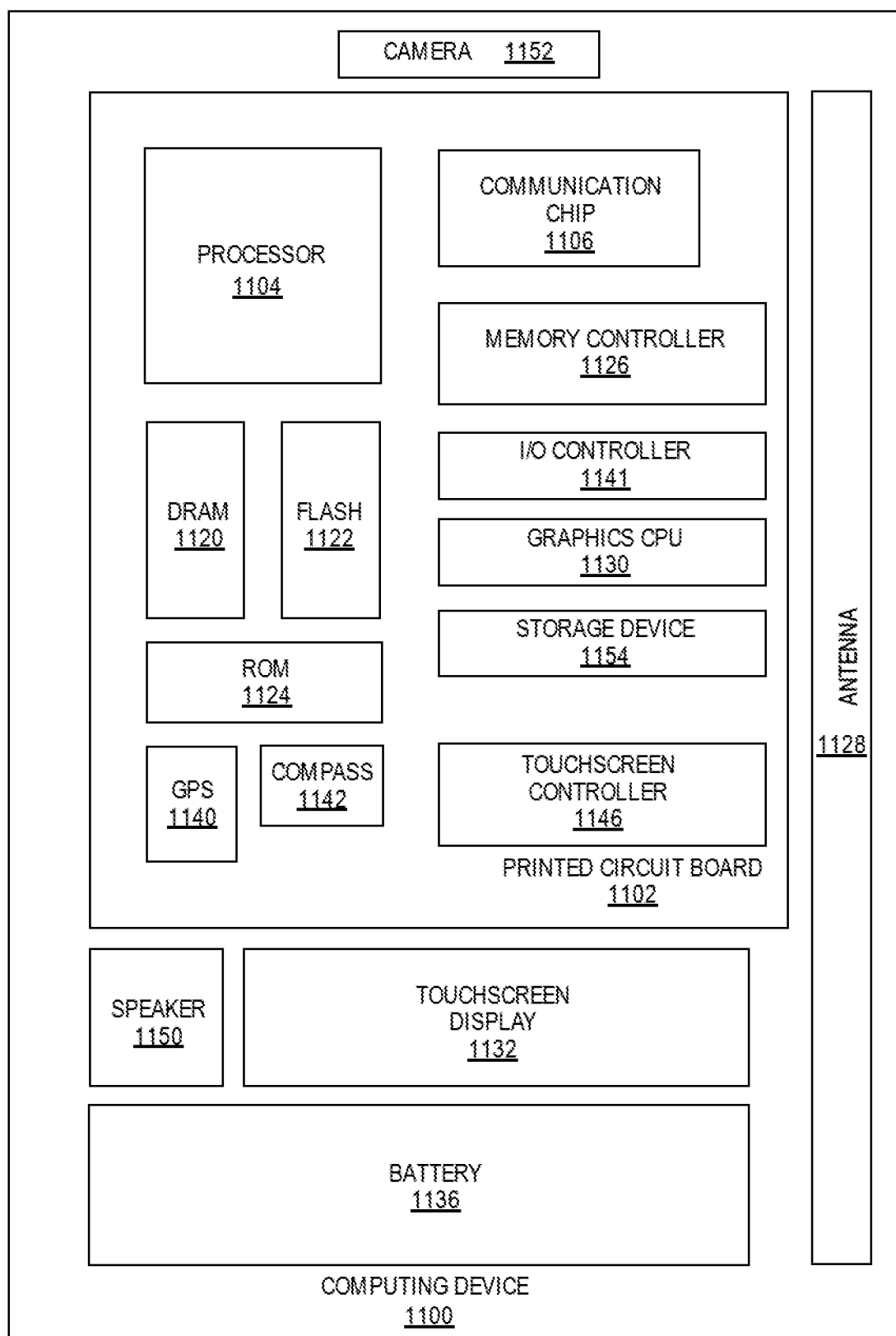


FIG. 10

**FIG. 11**

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SEMICONDUCTOR PACKAGES WITH CHIPLETS COUPLED TO A MEMORY DEVICE

TECHNICAL FIELD

The present disclosure relates to the field of electronic circuits. More particularly, the present disclosure relates to semiconductor packages with chiplet and memory device coupling.

BACKGROUND

The background description provided herein is for the purpose of generally presenting the context of the disclosure. Unless otherwise indicated herein, the materials described in this section are not prior art to the claims in this application and are not admitted to be prior art by inclusion in this section.

Legacy memory interconnect approaches have one active die communicating with one or more memory devices. For example, the active die size is paired with one or more memory dies. In particular, the active die size memory physical layer (PHY) input/output (I/O) width matches the width of the memory device I/O at a ratio of roughly 1 to 1.

BRIEF DESCRIPTION OF THE DRAWINGS

Embodiments will be readily understood by the following detailed description in conjunction with the accompanying drawings. To facilitate this description, like reference numerals designate like structural elements. Embodiments are illustrated by way of example, and not by way of limitation, in the figures of the accompanying drawings.

FIG. 1 illustrates a top view of an example semiconductor package, according to various embodiments.

FIG. 2 illustrates a cross-sectional, side view of the example semiconductor package of FIG. 1, according to various embodiments.

FIG. 3 illustrates a top view of another example semiconductor package, according to various embodiments.

FIG. 4 illustrates a cross-sectional, side view of the example semiconductor package of FIG. 3, according to various embodiments.

FIG. 5 illustrates a representation of an example semiconductor package arrangement, according to various embodiments.

FIG. 6 illustrates a representation of another example semiconductor package arrangement, according to various embodiments.

FIG. 7 illustrates a representation of another example semiconductor package arrangement, according to various embodiments.

FIG. 8 illustrates a representation of another example semiconductor package arrangement, according to various embodiments.

FIG. 9 illustrates a representation of another example semiconductor package arrangement, according to various embodiments.

FIG. 10 illustrates a portion of an example computer device, according to various embodiments.

FIG. 11 illustrates an example computer device that may employ the apparatuses and/or methods described herein, in accordance with various embodiments.

DETAILED DESCRIPTION

Apparatuses, devices and systems associated with semiconductor packages with chiplet and memory device coupling are disclosed herein.

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In embodiments, a semiconductor package may include a first chiplet, a second chiplet, and a memory device. The semiconductor package may further include an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device.

In the following detailed description, reference is made to the accompanying drawings which form a part hereof wherein like numerals designate like parts throughout, and in which is shown by way of illustration embodiments that may be practiced. It is to be understood that other embodiments may be utilized and structural or logical changes may be made without departing from the scope of the present disclosure. Therefore, the following detailed description is not to be taken in a limiting sense, and the scope of embodiments is defined by the appended claims and their equivalents.

Aspects of the disclosure are disclosed in the accompanying description. Alternate embodiments of the present disclosure and their equivalents may be devised without parting from the spirit or scope of the present disclosure. It should be noted that like elements disclosed below are indicated by like reference numbers in the drawings.

Various operations may be described as multiple discrete actions or operations in turn, in a manner that is most helpful in understanding the claimed subject matter. However, the order of description should not be construed as to imply that these operations are necessarily order dependent. In particular, these operations may not be performed in the order of presentation. Operations described may be performed in a different order than the described embodiment. Various additional operations may be performed and/or described operations may be omitted in additional embodiments.

For the purposes of the present disclosure, the phrase “A and/or B” means (A), (B), or (A and B). For the purposes of the present disclosure, the phrase “A, B, and/or C” means (A), (B), (C), (A and B), (A and C), (B and C), or (A, B and C).

The description may use the phrases “in an embodiment,” or “in embodiments,” which may each refer to one or more of the same or different embodiments. Furthermore, the terms “comprising,” “including,” “having,” and the like, as used with respect to embodiments of the present disclosure, are synonymous.

As used herein, the term “circuitry” may refer to, be part of, or include an Application Specific Integrated Circuit (ASIC), an electronic circuit, a processor (shared, dedicated, or group) and/or memory (shared, dedicated, or group) that execute one or more software or firmware programs, a combinational logic circuit, and/or other suitable components that provide the described functionality.

FIG. 1 illustrates a top view of an example semiconductor package 100, according to various embodiments. In particular, FIG. 1 illustrates a simplified top view of the semiconductor package 100 to illustrate certain features.

The semiconductor package 100 includes a substrate assembly 102. The substrate assembly 102 includes a substrate with one or more layers located on the substrate. The layers can include dielectric material, conductive elements (such as traces, vias, and/or conductive planes), or some combination thereof.

The semiconductor package 100 further includes a plurality of chiplets 104. For example, the semiconductor package 100 includes a first chiplet 104a, a second chiplet 104b, a third chiplet 104c, and a fourth chiplet 104d in the illustrated embodiment. The chiplets 104 are mounted to a

surface of the substrate assembly **102**. Each of the chiplets **104** can comprise a miniscule circuit that may be coupled with other chiplets to produce an electronic component, such as a microprocessor and/or a chip. In some embodiments, each of the chiplets **104** may have an area of between 20 square millimeters (mm²) and 400 mm². Utilizing chiplets may provide for more good dies per wafer, greater flexibility to bin based on performance/leakage, and greater flexibility to scale the die complex size (logic elements or cores) for different product applications than larger dies.

The semiconductor package **100** further includes a memory device **106**. The memory device **106** is mounted to the same surface of the substrate assembly **102** as the chiplets **104**. The memory device **106** may be a high bandwidth memory (HBM) device (such as an HBM dynamic random-access memory (DRAM) device, an HBM2 device, and/or an HBM3 device) in some embodiments. Further, the memory device **106** may be a high performance, high bandwidth memory device in some embodiments.

The memory device **106** includes a plurality of memory channels that support communication with the memory device **106**. For example, each of the memory channels provide access to the memory device **106** for storage and retrieval of data from the memory device **106**. In some embodiments, the memory channels may be grouped into channel clusters, where each channel cluster includes one or more of the memory channels. For example, the memory device **106** may include eight memory channels in some embodiments, where each of the channel clusters includes two memory channels or four memory channels. Each memory channel may have its own clock, the memory channels may share a clock, or some combination thereof.

The memory device **106** includes a PHY I/O. The PHY I/O can be a centralized PHY I/O or a distributed PHY I/O. For centralized PHY I/O, a single PHY I/O may be utilized by all the memory channels of the memory device **106**. For distributed PHY I/O, the memory device **106** includes a plurality of PHY I/Os, where each of the PHY I/Os may be utilized by one or more of the memory channels. For example, a first and a second memory channel may utilize one of the distributed PHY I/Os, while a third and a fourth memory channel may utilize another of the distributed PHY I/Os. In some embodiments, the PHY I/O are separated into I/O quadrants, where the quadrants can match a floor plan of the memory device **106**. In some embodiments, distributed PHY I/O may reduce the I/O power of the memory device **106**, and achieve high bandwidth and high performance.

The semiconductor package **100** further includes an interconnect structure **108**. The interconnect structure **108** couples the chiplets **104** to the memory device **106**. In some embodiments, the interconnect structure **108** includes one or more embedded multi-die interconnect bridges (EMIBs), where each of the EMIBs are embedded within the substrate assembly **102**. The substrate assembly **102** includes conductive elements that couple the chiplets **104** and the memory device **106** to the EMIBs. Each of the EMIBs include a piece of passive silicon with conductive elements located within the passive silicon for conducting signals. In other embodiments, the interconnect structure **108** may include active EMIBs with repeaters designed into the bridge, interposers (such as silicon interposers, organic interposers, or other interposers known in the art), fan out wafer level structures, or some combination thereof.

In the illustrated embodiment, the interconnect structure **108** includes a first EMIB **108a**, a second EMIB **108b**, a third EMIB **108c**, and a fourth EMIB **108d**. The first EMIB

108a couples the first chiplet **104a** to the memory device **106**, the second EMIB **108b** couples the second chiplet **104b** to the memory device **106**, the third EMIB **108c** couples the third chiplet **104c** to the memory device **106**, and the fourth EMIB **108d** couples the fourth chiplet **104d** to the memory device **106**. Each of the EMIBs can couple each of the chiplets **104** to different channel clusters of the memory device **106**, where each channel cluster includes one or more memory channels. For example, the first EMIB **108a** can couple the first chiplet **104a** to a first channel cluster, the second EMIB **108b** can couple the second chiplet **104b** to a second channel cluster, the third EMIB **108c** can couple the third chiplet **104c** to a third channel cluster, and the fourth EMIB **108d** can couple the fourth chiplet **104d** to a fourth channel cluster. Further, each of the EMIBs can couple each of the chiplets **104** to a centralized PHY I/O or to different distributed PHY I/Os. For example, the first EMIB **108a** can couple the first chiplet **104a** to a first distributed PHY I/O, the second EMIB **108b** can couple the second chiplet **104b** to a second distributed PHY I/O, the third EMIB **108c** can couple the third chiplet **104c** to a third distributed PHY I/O, and the fourth EMIB **108d** can couple the fourth chiplet **104d** to a fourth distributed PHY I/O.

While the illustrated embodiment shows four chiplets **104** and four EMIBs **108**, it is to be understood that there may be more or fewer chiplets **104** and/or more or fewer EMIBs **108** in other embodiments. For example, the semiconductor package **100** can include four chiplets **104** and two EMIBs **108** in other embodiments, where a first of the EMIBs **108** couples two of the chiplets **104** to the memory device **106** and a second of the EMIBs **108** couples the other two of the chiplets **104** to the memory device **106**. Further, the EMIBs **108** may couple two or more of the chiplets **104** together in some embodiments. The chiplets **104** coupled with each other via the EMIBs **108** may utilize the EMIBs **108** for communication between the chiplets **104**, the communication including clock distribution communications, register control communications, interface testing function communications, or some combination thereof.

FIG. 2 illustrates a cross-sectional, side view of the example semiconductor package **100** of FIG. 1, according to various embodiments. In particular, FIG. 2 illustrates the first chiplet **104a**, the third chiplet **104c**, and the memory device **106** mounted to the substrate assembly **102**. Further, the first EMIB **108a** and the third EMIB **108c** are embedded within the substrate assembly **102**.

The semiconductor package **100** further includes a plurality of interconnect elements **200**. The interconnect elements **200** couple the first chiplet **104a**, the third chiplet **104c**, and the memory device **106** to conductive elements **204** of the substrate assembly **102**. For example, the interconnect elements **200** couple the first chiplet **104a**, the third chiplet **104c**, and the memory device **106** to pads of the conductive elements **204**, the pads located at a surface of the substrate assembly **102**. In the illustrated embodiment, the interconnect elements **200** are illustrated as a ball grid array. In other embodiments, the interconnect elements **200** may be a ball grid array, a land grid array, a column grid array, or some combination thereof.

The conductive elements **204** couple some of the interconnect elements **200** to the first EMIB **108a** and the third EMIB **108c**. For example, the conductive elements **204** couple a first portion **200a** of the interconnect elements **200** and a second portion **200b** of the interconnect elements **200** to the first EMIB **108a**, where the first portion **200a** is coupled to the first chiplet **104a** and the second portion **200b** is coupled to the memory device **106**. Further, the conduc-

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tive elements **204** couple a third portion **200c** of the interconnect elements **200** and a fourth portion **200d** of the interconnect elements **200** to the third EMIB **108c**, where the third portion **200c** is coupled to the memory device **106** and the fourth portion is coupled to the third chiplet **104c**.

The first EMIB **108a** includes one or more conductive paths **206** that couple a portion of the conductive elements **204** coupled to the first chiplet **104a** with a portion of the conductive elements **204** coupled to the memory device **106**. Accordingly, the first EMIB **108a** provides for communication between the first chiplet **104a** and the memory device **106** via the conductive paths **206**. For example, the conductive paths **206** of the first EMIB **108a** can provide for exchange of data between the first chiplet **104a** and the memory device **106**, the data for storage on the memory device **106** and/or being retrieved from the memory device **106**.

The third EMIB **108c** includes one or more conductive paths **208** that couple a portion of the conductive elements **204** coupled to the memory device **106** with a portion of the conductive elements **204** coupled to the third chiplet **104c**. Accordingly, the third EMIB **108c** provides for communication between the third chiplet **104c** and the memory device **106** via the conductive paths **208**. For example, the conductive paths **208** of the third EMIB **108c** can provide for exchange of data between the first chiplet **104a** and the memory device **106**, the data for storage on the memory device **106** and/or being retrieved from the memory device **106**.

FIG. 3 illustrates a top view of another example semiconductor package **300**, according to various embodiments. In particular, FIG. 3 illustrates a simplified top view of the semiconductor package **300** to illustrate certain features.

The semiconductor package **300** includes a substrate assembly **302**. The substrate assembly **302** includes one or more of the features of the substrate assembly **102** (FIG. 1). In particular, the substrate assembly **302** includes a substrate with one or more layers located on the substrate. The layers can include dielectric material, conductive elements (such as traces, vias, and/or conductive planes), or some combination thereof.

The semiconductor package **300** further includes an interconnect structure **304**. In the illustrated embodiment, the interconnect structure **304** comprises an interposer. The interposer is mounted to a surface of the substrate assembly **302**. The interposer can be passive or active silicon with one or more conductive paths located within the silicon. The conductive paths couple to some of the conductive elements of the substrate assembly **302** at a first side of the interposer and extend to a second side of the interposer. In some embodiments, some of the conductive paths may extend between pads located at the second side of the interposer.

The semiconductor package **300** further includes a plurality of chiplets **306**. For example, the semiconductor package **300** includes a first chiplet **306a**, a second chiplet **306b**, a third chiplet **306c**, and a fourth chiplet **306d**. The plurality of chiplets **306** include one or more of the features of the plurality of chiplets **104** (FIG. 1). The plurality of chiplets **306** are mounted to the interconnect structure **304** on an opposite side of the interconnect structure **304** from the substrate assembly **302**. Further, each of the plurality of chiplets **306** are coupled to one or more of the conductive paths of the interconnect structure **304**.

The semiconductor package **300** further includes a memory device **308**. The memory device **308** includes one or more of the features of the memory device **106** (FIG. 1). The memory device **308** is mounted to the interconnect

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structure **304** on an opposite side of the interconnect structure **304** from the substrate assembly **302**. Further, the memory device **308** is coupled to one or more of the conductive paths of the interconnect structure **304**.

The interconnect structure **304** couples each of the plurality of chiplets **306** to the memory device **308**. In particular, the conductive pathways couple each of the plurality of chiplets **306** to the memory device **308** and provides for conduction of signals between each of the plurality of chiplets **306** and the memory device **308**. The interconnect structure **304** can couple each of the plurality of chiplets to different channel clusters of the memory device **308**, where each channel cluster includes one or more memory channels of the memory device **308**. For example, the interconnect structure **304** can couple the first chiplet **306a** to a first channel cluster, the second chiplet **306b** to a second channel cluster, the third chiplet **306c** to a third channel cluster, and the fourth chiplet **306d** to a fourth channel cluster. Further, the interconnect structure **304** can couple each of the chiplets **306** to a centralized PHY I/O of the memory device **308** or to different distributed PHY I/Os of the memory device **308**.

In some embodiments, the interconnect structure **304** can further couple one or more of the chiplets **306** to one or more of the other chiplets **306**. For example, the interconnect structure **304** can couple the first chiplet **306a** to the second chiplet **306b**. The chiplets **306** coupled to each other via the interconnect structure **304** may utilize the interconnect structure **304** for communication between the chiplets **306**, the communication including clock distribution communications, register control communications, interface testing function communications, or some combination thereof. While the illustrated embodiment shows four chiplets **306**, it is to be understood that there may be more or fewer chiplets **306** in other embodiments.

FIG. 4 illustrates a cross-sectional, side view of the example semiconductor package **300** of FIG. 3, according to various embodiments. In particular, FIG. 4 illustrates the interconnect structure **304** mounted to the substrate assembly **302**. Further, the first chiplet **306a**, the third chiplet **306c**, and the memory device **308** are mounted to the interconnect structure **304**.

The semiconductor package **300** includes a first plurality of interconnect elements **402** that couple the interconnect structure **304** to conductive elements **404** (such as traces, vias, and/or conductive planes) of the substrate assembly **302**. For example, the interconnect elements **402** couple the interconnect structure **304** to pads of the conductive elements **404**. In the illustrated embodiment, the interconnect elements **402** are illustrated as a ball grid array. In other embodiments, the interconnect elements **402** may be a ball grid array, a land grid array, a column grid array, or some combination thereof.

The semiconductor package **300** further includes a second plurality of interconnect elements **406**. The interconnect elements **406** couple the first chiplet **306a**, the third chiplet **306c**, and the memory device **308** to the interconnect structure **304**. In the illustrated embodiment, the interconnect elements **406** are illustrated as a ball grid array. In other embodiments, the interconnect elements **406** may be a ball grid array, a land grid array, a column grid array, or some combination thereof.

The interconnect structure **304** includes one or more conductive paths **408**. A portion of the conductive paths **408** can couple the substrate assembly **302** to the first chiplet **306a**, the third chiplet **306c**, and/or the memory device **308**. Further, a portion of the conductive paths **408** can couple the

first chiplet **306a** to the memory device **308** and the third chiplet **306c** to the memory device **308**. Accordingly, the conductive paths **408** provide for communication among the substrate assembly **302**, the first chiplet **306a**, the third chiplet **306c**, and the memory device **308**. For example, the conductive paths **408** can provide for exchange of data between the first chiplet **306a** and the memory device **308**, and the third chiplet **306c** and the memory device **308**, the data for storage on the memory device **308** and/or being retrieved from the memory device **308**.

In other embodiments, the conductive paths **408** may further couple one or more of the chiplets **306** together. For example, the conductive paths **408** may couple the first chiplet **306a** and the third chiplet **306c**. The conductive paths **408** may provide for communication between the chiplets **306**, the communication including clock distribution communications, register control communications, interface testing function communications, or some combination thereof.

FIG. **5** illustrates a representation **500** of an example semiconductor package arrangement, according to various embodiments. In particular, the representation **500** illustrates coupling among chiplets **502** and a memory device **504** in some embodiments. The chiplets **502** include one or more of the features of the chiplets **104** (FIG. **1**) and/or the chiplets **306** (FIG. **3**). Further, the memory device **504** includes one or more of the features of the memory device **106** (FIG. **1**) and/or the memory device **308** (FIG. **3**). The coupling may be implemented by an interconnect structure (such as the interconnect structure **108** (FIG. **1**), the interconnect structure **304** (FIG. **3**), and/or fan out wafer level structures), as is described further in relation to FIG. **5**. The chiplets **502**, the memory device **504**, and the interconnect structure may be implemented within a semiconductor package, such as the semiconductor package **100** (FIG. **1**) and/or the semiconductor package **300** (FIG. **3**).

In the illustrated embodiment, the memory device **504** includes eight memory channels. The memory channels are clustered into four channel clusters: first channel cluster **506**, second channel cluster **508**, third channel cluster **510**, and fourth channel cluster **512**. Each channel cluster includes two memory channels. In particular, the first channel cluster **506** includes a first memory channel (which may be referred to as "Channel A") and a second memory channel (which may be referred to as "Channel B"). The second channel cluster **508** includes a third memory channel (which may be referred to as "Channel C") and a fourth memory channel (which may be referred to as "Channel D"). The third channel cluster **510** includes a fifth memory channel (which may be referred to as "Channel E") and a sixth memory channel (which may be referred to as "Channel F"). The fourth channel cluster **512** includes a seventh memory channel (which may be referred to as "Channel G") and an eighth memory channel (which may be referred to as "Channel H"). In other embodiments, the memory device **504** may have more or fewer memory channels, the memory device **504** may have more or fewer channel clusters, and/or the channel clusters may include different allocations of the memory channels.

The chiplets **502** include a first chiplet **502a**, a second chiplet **502b**, a third chiplet **502c**, and a fourth chiplet **502d**. The chiplets **502** may be included in a single die complex, may be included in separate die complexes, may not be included in a die complex, or some combination thereof. Each of the chiplets **502** are coupled to different ones of the channel clusters. In particular, the first chiplet **502a** is coupled to the first channel cluster **506**, the second chiplet

502b is coupled to the third channel cluster **510**, the third chiplet **502c** is coupled to the second channel cluster **508**, and the fourth chiplet **502d** is coupled to the fourth channel cluster **512**. Each of the chiplets **502** can utilize the respective channel cluster to store data in and retrieve data from the memory device **504**. Each of the chiplets **502** have a PHY I/O that is one-quarter of the PHY I/O of the memory device **504**. For example, each of the PHY I/O of the chiplets **502** may be the same size of PHY I/O associated with each of the channel clusters. Further, the chiplets **502** may be coupled to each other. For example, the chiplets **502** may share clocking generation and control circuits. The chiplets **502** being coupled can allow for communication among the chiplets **502**, including clock tree distribution communications, register control communications, interface testing function communications, or some combination thereof.

The representation **500** further includes a plurality of memory controllers **514**. Each of the chiplets **502** has one of the memory controllers **514**. In particular, the first chiplet **502a** has a first memory controller **514a**, the second chiplet **502b** has a second memory controller **514b**, the third chiplet **502c** has a third memory controller **514c**, and the fourth chiplet **502d** has a fourth memory controller **514d**. Each of the memory controllers **514** may facilitate communication of the corresponding chiplets **502** with the memory device **504**. Further, the memory controllers **514** are coupled to each other. Accordingly, the memory controllers **514** can communicate among themselves, including register control communications, interface testing function communications, or some combination thereof. For example, the memory controllers **514** may implement interface testing functions (such as IEEE 1500). In other embodiments, the representation **500** may include a single memory controller that is coupled to all of the chiplets **502**.

FIG. **6** illustrates a representation **600** of another example semiconductor package arrangement, according to various embodiments. In particular, the representation **600** illustrates coupling among chiplets **602** and a memory device **604** in some embodiments. The chiplets **602** include one or more of the features of the chiplets **104** (FIG. **1**) and/or the chiplets **306** (FIG. **3**). Further, the memory device **604** includes one or more of the features of the memory device **106** (FIG. **1**) and/or the memory device **308** (FIG. **3**). The chiplets **602** and the memory device **604** may be implemented within a semiconductor package, such as the semiconductor package **100** (FIG. **1**) and/or the semiconductor package **300** (FIG. **3**).

In the illustrated embodiment, the memory device **604** includes four channel clusters: first channel cluster **606**, second channel cluster **608**, third channel cluster **610**, and fourth channel cluster **612**. Each of the channel clusters includes one or more memory channels of the memory device **604**. In some embodiments, the memory device **604** may include eight memory channels, where each of the channel clusters includes two memory channels. In other embodiments, there may be more or fewer channel clusters, more or fewer memory channels, different allocations of memory channels among the channel clusters, or some combination thereof. Further, the memory device **604** includes a centralized PHY I/O **614**. The centralized PHY I/O **614** can include the four channel clusters.

The chiplets **602** include a first chiplet **602a** and a second chiplet **602b**. The chiplets **602** may be included in a single die complex, may be included in separate die complexes, may not be included in a die complex, or some combination thereof. The first chiplet **602a** is coupled to the first channel cluster **606** and the second channel cluster **608**. The first

chiplet **602a** can utilize the first channel cluster **606** and/or the second channel cluster **608** to store data in and retrieve data from the memory device **604**. The second chiplet **602b** is coupled to the third channel cluster **610** and the fourth channel cluster **612**. The second chiplet **602b** can utilize the third channel cluster **610** and/or the fourth channel cluster **612** to store data in and retrieve data from the memory device **604**. The first chiplet **602a** and the second chiplet **602b** are further coupled to each other. The first chiplet **602a** and the second chiplet **602b** can communicate with each other, including clock distribution communications, register control communications, interface testing function communications, or some combination thereof.

The representation **600** further includes an interconnect structure that provides the coupling among the first chiplet **602a**, the second chiplet **602b**, and the memory device **604**. In particular, the interconnect structure is illustrated as an EMIB **616** in the illustrated embodiments. The EMIB **616** includes one or more of the features of the first EMIB **108a** (FIG. 1), the second EMIB **108b** (FIG. 1), the third EMIB **108c** (FIG. 1), and/or the fourth EMIB **108d** (FIG. 1). The EMIB **616** can provide the coupling between the first chiplet **602a** and the memory device **604**, the second chiplet **602b** and the memory device **604**, the first chiplet **602a** and the second chiplet **602b**, or some combination thereof. In other embodiments, the interconnect structure may be implemented as one or more EMIBs (such as the first EMIB **108a**, the second EMIB **108b**, the third EMIB **108c**, and/or the fourth EMIB **108d** (FIG. 1)), an interposer (such as the interposer described in relation to FIG. 3 and FIG. 4), fan out wafer level structures, or some combination thereof. A tile channel **618** may further be coupled to the first chiplet **602a** and the second chiplet **602b** in embodiments where the first chiplet **602a** and the second chiplet **602b** are tiled. In other embodiments, the tile channel **618** may be omitted.

FIG. 7 illustrates a representation **700** of another example semiconductor package arrangement, according to various embodiments. In particular, the representation **700** illustrates coupling among chiplets **702** and a memory device **704** in some embodiments. The chiplets **702** include one or more of the features of the chiplets **104** (FIG. 1) and/or the chiplets **306** (FIG. 3). Further, the memory device **704** includes one or more of the features of the memory device **106** (FIG. 1) and/or the memory device **308** (FIG. 3). The chiplets **702** and the memory device **704** may be implemented within a semiconductor package, such as the semiconductor package **100** (FIG. 1) and/or the semiconductor package **300** (FIG. 3).

In the illustrated embodiment, the memory device **704** includes four channel clusters: first channel cluster **706**, second channel cluster **708**, third channel cluster **710**, and fourth channel cluster **712**. Each of the channel clusters includes one or more memory channels of the memory device **704**. In some embodiments, the memory device **704** may include eight memory channels, where each of the channel clusters includes two memory channels. In other embodiments, there may be more or fewer channel clusters, more or fewer memory channels, different allocations of memory channels among the channel clusters, or some combination thereof. Further, the memory device **704** includes a centralized PHY I/O **714**. The centralized PHY I/O **714** can include the four channel clusters.

The chiplets **702** include a first chiplet **702a**, a second chiplet **702b**, a third chiplet **702c**, and a fourth chiplet **702d**. The chiplets **702** may be included in a single die complex, may be included in separate die complexes, may not be included in a die complex, or some combination thereof.

Each of the chiplets **702** are coupled to different ones of the channel clusters. For example, the first chiplet **702a** is coupled to the first channel cluster **706**, the second chiplet **702b** is coupled to the second channel cluster **708**, the third chiplet **702c** is coupled to the third channel cluster **710**, and the fourth chiplet **702d** is coupled to the fourth channel cluster **712**. Each of the chiplets **702** can utilize the respective channel cluster to store data in and retrieve data from the memory device **704**. The first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, and the fourth chiplet **702d** are further coupled to each other. The first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, and the fourth chiplet **702d** can communicate with each other, including clock distribution communications, register control communications, interface testing function communications, or some combination thereof.

The representation **700** further includes an interconnect structure that provides the coupling among the first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, the fourth chiplet **702d**, and the memory device **704**. In particular, the interconnect structure is illustrated as an EMIB **716** in the illustrated embodiments. The EMIB **716** includes one or more of the features of the first EMIB **108a** (FIG. 1), the second EMIB **108b** (FIG. 1), the third EMIB **108c** (FIG. 1), and/or the fourth EMIB **108d** (FIG. 1). The EMIB **716** can provide the coupling between the first chiplet **702a** and the memory device **704**, the second chiplet **702b** and the memory device **704**, the third chiplet **702c** and the memory device **704**, the fourth chiplet **702d** and the memory device **704**, the first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, and the fourth chiplet **702d**, or some combination thereof. In other embodiments, the interconnect structure may be implemented as one or more EMIBs (such as the first EMIB **108a**, the second EMIB **108b**, the third EMIB **108c**, and/or the fourth EMIB **108d** (FIG. 1)), an interposer (such as the interposer described in relation to FIG. 3 and FIG. 4), fan out wafer level structures, or some combination thereof. One or more tile channels **718** may further be coupled to the first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, and the fourth chiplet **702d** in embodiments where the first chiplet **702a**, the second chiplet **702b**, the third chiplet **702c**, and the fourth chiplet **702d** are tiled. In other embodiments, the tile channels **718** may be omitted.

FIG. 8 illustrates a representation **800** of another example semiconductor package arrangement, according to various embodiments. In particular, the representation **800** illustrates coupling among chiplets **802** and a memory device **804** in some embodiments. The chiplets **802** include one or more of the features of the chiplets **104** (FIG. 1) and/or the chiplets **306** (FIG. 3). Further, the memory device **804** includes one or more of the features of the memory device **106** (FIG. 1) and/or the memory device **308** (FIG. 3). The chiplets **802** and the memory device **804** may be implemented within a semiconductor package, such as the semiconductor package **100** (FIG. 1) and/or the semiconductor package **300** (FIG. 3).

In the illustrated embodiment, the memory device **804** includes four channel clusters: first channel cluster **806**, second channel cluster **808**, third channel cluster **810**, and fourth channel cluster **812**. Each of the channel clusters includes one or more memory channels of the memory device **804**. In some embodiments, the memory device **804** may include eight memory channels, where each of the channel clusters includes two memory channels. In other embodiments, there may be more or fewer channel clusters,

more or fewer memory channels, different allocations of memory channels among the channel clusters, or some combination thereof.

Further, the memory device **804** includes distributed PHY I/Os **814**. In particular, the memory device **804** includes a first PHY I/O **814a**, a second PHY I/O **814b**, a third PHY I/O **814c**, and a fourth PHY I/O **814d**. The PHY I/O of the memory device **804** is separated into I/O quadrants, where a first I/O quadrant **816** includes the first PHY I/O **814a**, a second I/O quadrant **818** includes the second PHY I/O **814b**, a third I/O quadrant **820** includes the third PHY I/O **814c**, and a fourth I/O quadrant **822** includes the fourth PHY I/O **814d**. Each of the PHY I/Os **814** have different channel clusters. For example, the first PHY I/O **814a** has the first channel cluster **806**, the second PHY I/O **814b** has the second channel cluster **808**, the third PHY I/O **814c** has the third channel cluster **810**, and the fourth PHY I/O **814d** has the fourth channel cluster **812**.

The chiplets **802** include a first chiplet **802a**, a second chiplet **802b**, a third chiplet **802c**, and a fourth chiplet **802d**. The chiplets **802** may be included in a single die complex, may be included in separate die complexes, may not be included in a die complex, or some combination thereof. Each of the chiplets **802** are coupled to different ones of the channel clusters. For example, the first chiplet **802a** is coupled to the first channel cluster **806**, the second chiplet **802b** is coupled to the second channel cluster **808**, the third chiplet **802c** is coupled to the third channel cluster **810**, and the fourth chiplet **802d** is coupled to the fourth channel cluster **812**. Each of the chiplets **802** can utilize the respective channel cluster to store data in and retrieve data from the memory device **804**.

The first chiplet **802a** and the second chiplet **802b** are coupled to each other. The first chiplet **802a** and the second chiplet **802b** can communicate with each other, including clock distribution communications, register control communications, interface testing function communications, or some combination thereof. Further, the third chiplet **802c** and the fourth chiplet **802d** are coupled to each other. The third chiplet **802c** and the fourth chiplet **802d** can communicate with each other, including clock distribution communications, register control communications, interface testing function communications, or some combination thereof.

The representation **800** further includes an interconnect structure that provides the coupling among the first chiplet **802a**, the second chiplet **802b**, the third chiplet **802c**, the fourth chiplet **802d**, and the memory device **804**. In particular, the interconnect structure is illustrated as a first EMIB **824** and a second EMIB **826** in the illustrated embodiments. The first EMIB **824** and the second EMIB **826** include one or more of the features of the first EMIB **108a** (FIG. 1), the second EMIB **108b** (FIG. 1), the third EMIB **108c** (FIG. 1), and/or the fourth EMIB **108d** (FIG. 1). The first EMIB **824** can provide the coupling between the first chiplet **802a** and the memory device **804**, the second chiplet **802b** and the memory device **804**, the first chiplet **802a** and the second chiplet **802b**, or some combination thereof. The second EMIB **826** can provide the coupling between the third chiplet **802c** and the memory device **804**, the fourth chiplet **802d** and the memory device **804**, the third chiplet **802c** and the fourth chiplet **802d**, or some combination thereof. In other embodiments, the interconnect structure may be implemented as one or more EMIBs (such as the first EMIB **108a**, the second EMIB **108b**, the third EMIB **108c**, and/or the fourth EMIB **108d** (FIG. 1)), an interposer (such as the interposer described in relation to FIG. 3 and FIG. 4), fan out wafer level structures, or some combination thereof. One or

more tile channels **828** may further be coupled to the first chiplet **802a**, the second chiplet **802b**, the third chiplet **802c**, and the fourth chiplet **802d** in embodiments where the first chiplet **802a**, the second chiplet **802b**, the third chiplet **802c**, and the fourth chiplet **802d** are tiled. In other embodiments, the tile channels **828** may be omitted.

FIG. 9 illustrates a representation **900** of another example semiconductor package arrangement, according to various embodiments. In particular, the representation **900** illustrates coupling among chiplets **902** and a memory device **904** in some embodiments. The chiplets **902** include one or more of the features of the chiplets **104** (FIG. 1) and/or the chiplets **306** (FIG. 3). Further, the memory device **904** includes one or more of the features of the memory device **106** (FIG. 1) and/or the memory device **308** (FIG. 3). The chiplets **902** and the memory device **904** may be implemented within a semiconductor package, such as the semiconductor package **100** (FIG. 1) and/or the semiconductor package **300** (FIG. 3).

In the illustrated embodiment, the memory device **904** includes four channel clusters: first channel cluster **906**, second channel cluster **908**, third channel cluster **910**, and fourth channel cluster **912**. Each of the channel clusters includes one or more memory channels of the memory device **904**. In some embodiments, the memory device **904** may include eight memory channels, where each of the channel clusters includes two memory channels. In other embodiments, there may be more or fewer channel clusters, more or fewer memory channels, different allocations of memory channels among the channel clusters, or some combination thereof.

Further, the memory device **904** includes distributed PHY I/Os **914**. In particular, the memory device **904** includes a first PHY I/O **914a**, a second PHY I/O **914b**, a third PHY I/O **914c**, and a fourth PHY I/O **914d**. The PHY I/O of the memory device **904** is separated into I/O quadrants, where a first I/O quadrant **916** includes the first PHY I/O **914a**, a second I/O quadrant **918** includes the second PHY I/O **914b**, a third I/O quadrant **920** includes the third PHY I/O **914c**, and a fourth I/O quadrant **922** includes the fourth PHY I/O **914d**. Each of the PHY I/Os **914** have different channel clusters. For example, the first PHY I/O **914a** has the first channel cluster **906**, the second PHY I/O **914b** has the second channel cluster **908**, the third PHY I/O **914c** has the third channel cluster **910**, and the fourth PHY I/O **914d** has the fourth channel cluster **912**.

The chiplets **902** include a first chiplet **902a** and a second chiplet **902b**. The chiplets **902** may be included in a single die complex, may be included in separate die complexes, may not be included in a die complex, or some combination thereof. Each of the chiplets **902** are coupled to different ones of the channel clusters. For example, the first chiplet **902a** is coupled to the first channel cluster **906** and the second channel cluster **908**, and the second chiplet **902b** is coupled to the third channel cluster **910** and the fourth channel cluster **912**. Each of the chiplets **902** can utilize the respective channel cluster to store data in and retrieve data from the memory device **904**.

The representation **900** further includes an interconnect structure that provides the coupling among the first chiplet **902a**, the second chiplet **902b**, and the memory device **904**. In particular, the interconnect structure is illustrated as a first EMIB **924** and a second EMIB **926** in the illustrated embodiments. The first EMIB **924** and the second EMIB **926** include one or more of the features of the first EMIB **108a** (FIG. 1), the second EMIB **108b** (FIG. 1), the third EMIB **108c** (FIG. 1), and/or the fourth EMIB **108d** (FIG. 1). The

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first EMIB **924** can provide the coupling between the first chiplet **902a** and the memory device **904**. The second EMIB **926** can provide the coupling between the second chiplet **902b** and the memory device **904**. In other embodiments, the interconnect structure may be implemented as one or more EMIBs (such as the first EMIB **108a**, the second EMIB **108b**, the third EMIB **108c**, and/or the fourth EMIB **108d** (FIG. 1)), an interposer (such as the interposer described in relation to FIG. 3 and FIG. 4), fan out wafer level structures, or some combination thereof.

FIG. 10 illustrates a portion of an example computer device **1000**, according to various embodiments. The computer device **1000** includes a printed circuit board (PCB) **1002**.

The computer device **1000** includes a semiconductor package **1004**. The semiconductor package **1004** is mounted to a surface of the PCB **1002**. The semiconductor package **1004** may implement one or more of the features the semiconductor packages (such as the semiconductor package **100** (FIG. 1) and/or the semiconductor package **300** (FIG. 3)) and/or the representations of semiconductor package arrangements (such as the representation **500** (FIG. 5), the representation **600** (FIG. 6), the representation **700** (FIG. 7), the representation **800** (FIG. 8), and/or the representation **900** (FIG. 9)), as described herein.

The semiconductor package **1004** includes a substrate assembly **1006**. The substrate assembly **1006** includes one or more of the features of the substrate assembly **102** (FIG. 1) and/or the substrate assembly **302** (FIG. 3). The substrate assembly **1006** is mounted and coupled to the PCB **1002**.

The semiconductor package **1004** further includes an interconnect structure **1008**. In the illustrated embodiment, the interconnect structure **1008** is illustrated as a first EMIB **1008a** and a second EMIB **1008b** embedded within the substrate assembly **1006**. The first EMIB **1008a** and the second EMIB **1008b** include one or more of the features of the first EMIB **108a** (FIG. 1), the second EMIB **108b** (FIG. 1), the third EMIB **108c** (FIG. 1), and/or the fourth EMIB **108d** (FIG. 1). In other embodiments, the interconnect structure **1008** may be one or more EMIBs (such as the first EMIB **108a**, the second EMIB **108b**, the third EMIB **108c**, and/or the fourth EMIB **108d** (FIG. 1)), an interposer (such as the interposer described in relation to FIG. 3 and FIG. 4) mounted on the substrate assembly **1006**, fan out wafer level structures, or some combination thereof.

The semiconductor package **1004** further includes a plurality of chiplets **1010**. In particular, the semiconductor package **1004** includes a first chiplet **1010a** and a second chiplet **1010b** in the illustrated embodiment. The chiplets **1010** include one or more of the features of the chiplets **104** (FIG. 1), the chiplets **306** (FIG. 3), the chiplets **502** (FIG. 5), the chiplets **602** (FIG. 6), the chiplets **702** (FIG. 7), the chiplets **802** (FIG. 8), and/or the chiplets **902** (FIG. 9). The chiplets **1010** are coupled to the interconnect structure **1008**. In embodiments where the interconnect structure **1008** includes EMIBs (as shown), the chiplets **1010** may be mounted on the substrate assembly **1006**. In embodiments where the interconnect structure **1008** includes an interposer, the chiplets **1010** may be mounted on the interposer (as shown in FIG. 3 and FIG. 4).

The semiconductor package **1004** further includes a memory device **1012**. The memory device **1012** includes one or more of the features of the memory device **106** (FIG. 1), the memory device **308** (FIG. 3), the memory device **504** (FIG. 5), the memory device **604** (FIG. 6), the memory device **704** (FIG. 7), the memory device **804** (FIG. 8), and/or the memory device **904** (FIG. 9). The memory device **1012**

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is coupled to the interconnect structure **1008**. In embodiments where the interconnect structure **1008** includes EMIBs (as shown), the memory device **1012** may be mounted on the substrate assembly **1006**. In embodiments where the interconnect structure **1008** includes an interposer, the memory device **1012** may be mounted on the interposer (as shown in FIG. 3 and FIG. 4).

The interconnect structure **1008** provides the coupling among the chiplets **1010** and the memory device **1012** according to the couplings among the chiplets and the memory devices described throughout this disclosure. For example, the interconnect structure **1008** may couple the chiplets **1010** with the memory device **1012**, the chiplets **1010** with each other, the substrate assembly **1006** with the chiplets **1010** and the memory device **1012**, or some combination thereof.

FIG. 11 illustrates an example computer device **1100** that may employ the apparatuses and/or methods described herein (e.g., the semiconductor package **100**, the semiconductor package **300**, the semiconductor package represented by the representation **500** (FIG. 5), the semiconductor package represented by the representation **600** (FIG. 6), the semiconductor package represented by the representation **700** (FIG. 7), the semiconductor package represented by the representation **800** (FIG. 8), the semiconductor package represented by the representation **900** (FIG. 9), and/or the computer device **1000** (FIG. 10)), in accordance with various embodiments. As shown, computer device **1100** may include a number of components, such as one or more processor(s) **1104** (one shown) and at least one communication chip **1106**. In various embodiments, the one or more processor(s) **1104** each may include one or more processor cores. In various embodiments, the at least one communication chip **1106** may be physically and electrically coupled to the one or more processor(s) **1104**. In further implementations, the communication chip **1106** may be part of the one or more processor(s) **1104**. In various embodiments, computer device **1100** may include printed circuit board (PCB) **1102**. For these embodiments, the one or more processor(s) **1104** and communication chip **1106** may be disposed thereon. In alternate embodiments, the various components may be coupled without the employment of PCB **1102**.

Depending on its applications, computer device **1100** may include other components that may or may not be physically and electrically coupled to the PCB **1102**. These other components include, but are not limited to, memory controller **1126**, volatile memory (e.g., dynamic random access memory (DRAM) **1120**), non-volatile memory such as read only memory (ROM) **1124**, flash memory **1122**, storage device **1154** (e.g., a hard-disk drive (HDD)), an I/O controller **1141**, a digital signal processor (not shown), a crypto processor (not shown), a graphics processor **1130**, one or more antenna **1128**, a display (not shown), a touch screen display **1132**, a touch screen controller **1146**, a battery **1136**, an audio codec (not shown), a video codec (not shown), a global positioning system (GPS) device **1140**, a compass **1142**, an accelerometer (not shown), a gyroscope (not shown), a speaker **1150**, a camera **1152**, and a mass storage device (such as hard disk drive, a solid state drive, compact disk (CD), digital versatile disk (DVD)) (not shown), and so forth.

In some embodiments, the one or more processor(s) **1104**, flash memory **1122**, and/or storage device **1154** may include associated firmware (not shown) storing programming instructions configured to enable computer device **1100**, in response to execution of the programming instructions by one or more processor(s) **1104**, to practice all or selected

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aspects of the methods described herein. In various embodiments, these aspects may additionally or alternatively be implemented using hardware separate from the one or more processor(s) 1104, flash memory 1122, or storage device 1154.

In various embodiments, one or more components of the computer device 1100 may implement the features of the semiconductor packages (such as the semiconductor package 100, the semiconductor package 300, the semiconductor package represented by the representation 500 (FIG. 5), the semiconductor package represented by the representation 600 (FIG. 6), the semiconductor package represented by the representation 700 (FIG. 7), the semiconductor package represented by the representation 800 (FIG. 8), and/or the semiconductor package represented by the representation 900 (FIG. 9)) described herein. For example, the processor 1104, the communication chip 1106, the memory controller 1126, the I/O controller 1141, the graphics CPU 1130, the touch screen controller 1146, the GPS 1140, the compass 1142, or some combination thereof, may implement the features of the semiconductor packages.

The communication chips 1106 may enable wired and/or wireless communications for the transfer of data to and from the computer device 1100. The term “wireless” and its derivatives may be used to describe circuits, devices, systems, methods, techniques, communications channels, etc., that may communicate data through the use of modulated electromagnetic radiation through a non-solid medium. The term does not imply that the associated devices do not contain any wires, although in some embodiments they might not. The communication chip 1106 may implement any of a number of wireless standards or protocols, including but not limited to IEEE 802.20, Long Term Evolution (LTE), LTE Advanced (LTE-A), General Packet Radio Service (GPRS), Evolution Data Optimized (Ev-DO), Evolved High Speed Packet Access (HSPA+), Evolved High Speed Downlink Packet Access (HSDPA+), Evolved High Speed Uplink Packet Access (HSUPA+), Global System for Mobile Communications (GSM), Enhanced Data rates for GSM Evolution (EDGE), Code Division Multiple Access (CDMA), Time Division Multiple Access (TDMA), Digital Enhanced Cordless Telecommunications (DECT), Worldwide Interoperability for Microwave Access (WiMAX), Bluetooth, derivatives thereof, as well as any other wireless protocols that are designated as 3G, 4G, 5G, and beyond. The computer device 1100 may include a plurality of communication chips 1106. For instance, a first communication chip 1106 may be dedicated to shorter range wireless communications such as Wi-Fi and Bluetooth, and a second communication chip 1106 may be dedicated to longer range wireless communications such as GPS, EDGE, GPRS, CDMA, WiMAX, LTE, Ev-DO, and others.

In various implementations, the computer device 1100 may be a laptop, a netbook, a notebook, an ultrabook, a smartphone, a computer tablet, a personal digital assistant (PDA), an ultra-mobile PC, a mobile phone, a desktop computer, a server, a printer, a scanner, a monitor, a set-top box, an entertainment control unit (e.g., a gaming console or automotive entertainment unit), a digital camera, an appliance, a portable music player, or a digital video recorder. In further implementations, the computer device 1100 may be any other electronic device that processes data.

Example 1 may include a semiconductor package, comprising a first chiplet, a second chiplet, a memory device, and an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device.

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Example 2 may include the semiconductor package of example 1 or any other example herein, further including a substrate assembly, wherein the interconnect structure comprises an interposer located on the substrate assembly, and wherein the first chiplet, the second chiplet, and the memory device are mounted to the interposer on an opposite side of the interposer from the substrate assembly.

Example 3 may include the semiconductor package of example 1 or any other example herein, further including a substrate assembly, wherein the interconnect structure comprises an embedded multi-die interconnect bridge (EMIB) that is embedded with the substrate assembly, and wherein the first chiplet, the second chiplet, and the memory device are coupled to the EMIB.

Example 4 may include the semiconductor package of example 1 or any other example herein, further comprising a substrate assembly, wherein the interconnect structure including a first EMIB that is embedded within the substrate assembly, wherein the first EMIB couples the first chiplet to the first memory channel, and a second EMIB that is embedded within the substrate assembly, wherein the second EMIB couples the second chiplet to the second memory channel.

Example 5 may include the semiconductor package of example 1 or any other example herein, wherein the interconnect structure further couples a physical layer (PHY) of the first chiplet to a PHY of the second chiplet.

Example 6 may include the semiconductor package of example 1 or any other example herein, wherein the interconnect structure further couples a memory controller of the first chiplet to a memory controller of the second chiplet.

Example 7 may include the semiconductor package of example 1 or any other example herein, wherein the memory device includes eight memory channels, wherein the eight memory channels are broken up into a plurality of channel clusters, wherein the first chiplet is coupled to a first channel cluster of the plurality of channel clusters and the first channel cluster includes the first memory channel, and wherein the second chiplet is coupled to a second channel cluster of the plurality of channel clusters and the second channel cluster includes the second memory channel.

Example 8 may include the semiconductor package of example 7 or any other example herein, wherein the first channel cluster includes four memory channels and the second channel cluster includes four different memory channels.

Example 9 may include the semiconductor package of example 1 or any other example herein, wherein the interconnect structure is a first interconnect structure, and wherein the semiconductor package further includes a third chiplet, a fourth chiplet, and a second interconnect structure that couples the third chiplet to a third memory channel of the memory device and the fourth chiplet to a fourth memory channel of the memory device.

Example 10 may include the semiconductor package of example 1 or any other example herein, wherein the memory device comprises a high performance, high bandwidth memory device.

Example 11 may include the semiconductor package of example 1 or any other example herein, wherein the memory device comprises a high bandwidth memory dynamic random-access memory device.

Example 12 may include a computer device, including a printed circuit board (PCB), a semiconductor package mounted to the PCB, including a first chiplet, a second chiplet, a memory device that includes a plurality of memory channels separated into channel clusters, each of the channel

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clusters including at least one memory channel of the plurality of memory channels, and an interconnect structure that couples the first chiplet to a first channel cluster of the channel clusters and the second chiplet to a second channel cluster of the channel clusters, the memory device to store data for the first chiplet and the second chiplet.

Example 13 may include the computer device of example 12 or any other example herein, wherein the semiconductor package further comprises a substrate assembly, and wherein the interconnect structure comprises an interposer located on the substrate assembly.

Example 14 may include the computer device of example 12 or any other example herein, wherein the semiconductor package further includes a substrate assembly, and wherein the interconnect structure includes an embedded multi-die interconnect bridge (EMIB) that is embedded within the substrate assembly.

Example 15 may include the computer device of example 14 or any other example herein, wherein the EMIB is a first EMIB, and wherein the semiconductor package further includes a third chiplet, a fourth chiplet, and a second EMIB that is embedded within the substrate assembly, wherein the second EMIB couples the third chiplet and the fourth chiplet to the memory device.

Example 16 may include the computer device of example 14 or any other example herein, wherein the EMIB is a first EMIB, wherein the interconnect structure further includes a second EMIB that is embedded within the substrate assembly, wherein an input/output (I/O) physical layer (PHY) of the memory device is separated into I/O quadrants, wherein the first EMIB couples the first chiplet to a first I/O quadrant of the I/O quadrants, and wherein the second EMIB couples the second chiplet to a second I/O quadrant of the I/O quadrants.

Example 17 may include the computer device of example 12 or any other example herein, wherein the interconnect structure is a first interconnect structure, and wherein the semiconductor package further includes a third chiplet, a fourth chiplet, and a second interconnect structure that couples the third chiplet to a third channel cluster of the channel clusters and the fourth chiplet to a fourth channel cluster of the channel clusters.

Example 18 may include the computer device of example 17 or any other example herein, wherein each of the channel clusters includes two memory channels.

Example 19 may include the computer device of example 12 or any other example herein, wherein the memory device comprises a high bandwidth memory (HBM) device.

Example 20 may include the computer device of example 12 or any other example herein, wherein the memory device comprises a high bandwidth memory (HBM) dynamic random-access memory device.

It will be apparent to those skilled in the art that various modifications and variations can be made in the disclosed embodiments of the disclosed device and associated methods without departing from the spirit or scope of the disclosure. Thus, it is intended that the present disclosure covers the modifications and variations of the embodiments disclosed above provided that the modifications and variations come within the scope of any claims and their equivalents.

What is claimed is:

1. A semiconductor package, comprising:

a first chiplet comprising a first memory controller;

a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

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a memory device;

a substrate assembly; and

an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device, wherein the interconnect structure comprises:

a first EMIB that is embedded within the substrate assembly, wherein the first EMIB couples the first chiplet to the first memory channel; and

a second EMIB that is embedded within the substrate assembly, wherein the second EMIB couples the second chiplet to the second memory channel.

2. The semiconductor package of claim 1, wherein the interconnect structure comprises an interposer located on the substrate assembly, and wherein the first chiplet, the second chiplet, and the memory device are mounted to the interposer on an opposite side of the interposer from the substrate assembly.

3. The semiconductor package of claim 1, wherein the interconnect structure comprises an embedded multi-die interconnect bridge (EMIB) that is embedded with the substrate assembly, and wherein the first chiplet, the second chiplet, and the memory device are coupled to the EMIB.

4. The semiconductor package of claim 1, wherein the interconnect structure further couples a physical layer (PHY) of the first chiplet to a PHY of the second chiplet.

5. The semiconductor package of claim 1, wherein the interconnect structure couples the first memory controller of the first chiplet directly to the second memory controller of the second chiplet.

6. The semiconductor package of claim 1, wherein the memory device includes eight memory channels, wherein the eight memory channels are broken up into a plurality of channel clusters, wherein the first chiplet is coupled to a first channel cluster of the plurality of channel clusters and the first channel cluster includes the first memory channel, and wherein the second chiplet is coupled to a second channel cluster of the plurality of channel clusters and the second channel cluster includes the second memory channel.

7. The semiconductor package of claim 6, wherein the first channel cluster includes four memory channels and the second channel cluster includes four different memory channels.

8. The semiconductor package of claim 1, wherein the interconnect structure is a first interconnect structure, and wherein the semiconductor package further comprises:

a third chiplet;

a fourth chiplet; and

a second interconnect structure that couples the third chiplet to a third memory channel of the memory device and the fourth chiplet to a fourth memory channel of the memory device.

9. The semiconductor package of claim 1, wherein the memory device comprises a high performance, high bandwidth memory device.

10. The semiconductor package of claim 1, wherein the memory device comprises a high bandwidth memory dynamic random-access memory device.

11. A computer device, comprising:

a printed circuit board (PCB);

a semiconductor package mounted to the PCB, including:

a first chiplet comprising a first memory controller;

a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

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a memory device that includes a plurality of memory channels separated into channel clusters, each of the channel clusters including at least one memory channel of the plurality of memory channels; and
 an interconnect structure that couples the first chiplet to a first channel cluster of the channel clusters and the second chiplet to a second channel cluster of the channel clusters, the memory device to store data for the first chiplet and the second chiplet.

12. The computer device of claim 11, wherein the semiconductor package further comprises a substrate assembly, and wherein the interconnect structure comprises an interposer located on the substrate assembly.

13. The computer device of claim 11, wherein the semiconductor package further comprises a substrate assembly, and wherein the interconnect structure includes an embedded multi-die interconnect bridge (EMIB) that is embedded within the substrate assembly.

14. The computer device of claim 13, wherein the EMIB is a first EMIB, and wherein the semiconductor package further comprises:

- a third chiplet;
- a fourth chiplet; and

- a second EMIB that is embedded within the substrate assembly, wherein the second EMIB couples the third chiplet and the fourth chiplet to the memory device.

15. The computer device of claim 13, wherein the EMIB is a first EMIB, wherein the interconnect structure further includes a second EMIB that is embedded within the substrate assembly, wherein an input/output (I/O) physical layer (PHY) of the memory device is separated into I/O quadrants, wherein the first EMIB couples the first chiplet to a first I/O quadrant of the I/O quadrants, and wherein the second EMIB couples the second chiplet to a second I/O quadrant of the I/O quadrants.

16. The computer device of claim 11, wherein the interconnect structure is a first interconnect structure, and wherein the semiconductor package further includes:

- a third chiplet;
- a fourth chiplet; and

- a second interconnect structure that couples the third chiplet to a third channel cluster of the channel clusters and the fourth chiplet to a fourth channel cluster of the channel clusters.

17. The computer device of claim 16, wherein each of the channel clusters includes two memory channels.

18. The computer device of claim 11, wherein the memory device comprises a high bandwidth memory (HBM) device.

19. The computer device of claim 11, wherein the memory device comprises a high bandwidth memory (HBM) dynamic random-access memory device.

20. A semiconductor package, comprising:

- a first chiplet;

- a second chiplet;

- a third chiplet;

- a fourth chiplet;

- a memory device;

- a first interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device; and

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a second interconnect structure that couples the third chiplet to a third memory channel of the memory device and the fourth chiplet to a fourth memory channel of the memory device.

21. A semiconductor package, comprising:

- a first chiplet comprising a first memory controller;

- a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

- a memory device; and

- an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device, wherein the interconnect structure further couples a physical layer (PHY) of the first chiplet to a PHY of the second chiplet.

22. A semiconductor package, comprising:

- a first chiplet comprising a first memory controller;

- a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

- a memory device;

- a first interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device;

- a third chiplet;

- a fourth chiplet; and

- a second interconnect structure that couples the third chiplet to a third memory channel of the memory device and the fourth chiplet to a fourth memory channel of the memory device.

23. A semiconductor package, comprising:

- a first chiplet comprising a first memory controller;

- a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

- a memory device;

- a substrate assembly; and

- an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device, wherein the interconnect structure comprises an embedded multi-die interconnect bridge (EMIB) that is embedded with the substrate assembly, and wherein the first chiplet, the second chiplet, and the memory device are coupled to the EMIB.

24. A semiconductor package, comprising:

- a first chiplet comprising a first memory controller;

- a second chiplet comprising a second memory controller, the second memory controller coupled directly to the first memory controller;

- a memory device; and

- an interconnect structure that couples the first chiplet to a first memory channel of the memory device and the second chiplet to a second memory channel of the memory device, wherein the interconnect structure couples the first memory controller of the first chiplet directly to the second memory controller of the second chiplet.

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